

# RTE21N3M

Composite Transistor  
Zener Diode

Resistor Built-in Transistor Silicon NPN Epitaxial Type

## DESCRIPTION

RTE21N3M is a composite transistor built RT1N441 and Zener diode ( $V_Z=18V$ ) in SC-88 package.

Use of this product enables miniaturization of equipment and reduction parts and process.

## FEATURE

- This product is packaged in super mini PKG(6pin) and mount RT1N441( $R_1=47k\Omega$ ,  $R_2=47k\Omega$ ) and Zener diode( $V_Z=18V$ ).
- Enables miniaturization of equipment and high density mounting.

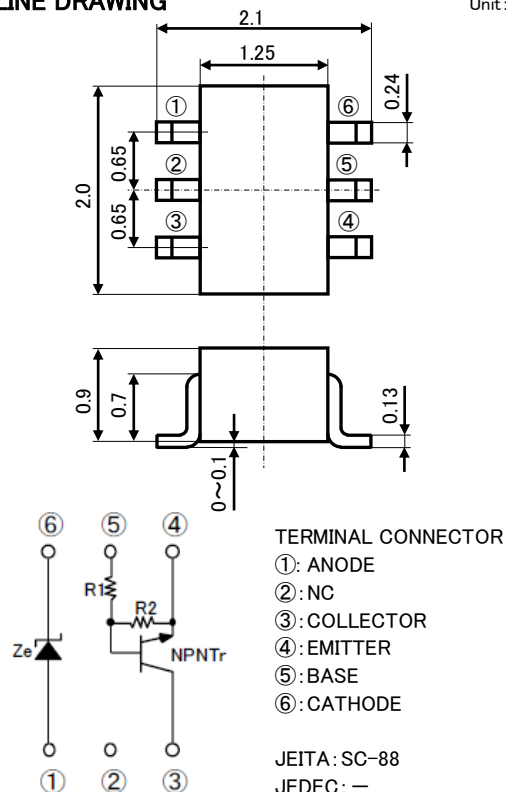
## APPLICATION

Power supply circuit

Driver circuit

## OUTLINE DRAWING

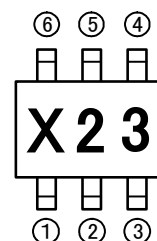
Unit: mm



## MAXIMUM RATING (Ta=25°C)

SYMBOL	PARAMETER	RATING	UNIT
V <sub>CB0</sub>	Collector to Base voltage	50	V
V <sub>EB0</sub>	Emitter to Base voltage	10	V
V <sub>CEO</sub>	Collector to Emitter voltage	50	V
V <sub>IN</sub>	Input voltage	40	V
I <sub>C</sub>	Collector current	100	mA
I <sub>CM</sub>	Peak Collector current	200	mA
P <sub>T</sub>	Total dissipation	150	mW
T <sub>j</sub>	Junction temperature	+150	°C
T <sub>stg</sub>	Storage temperature	-55~+150	°C

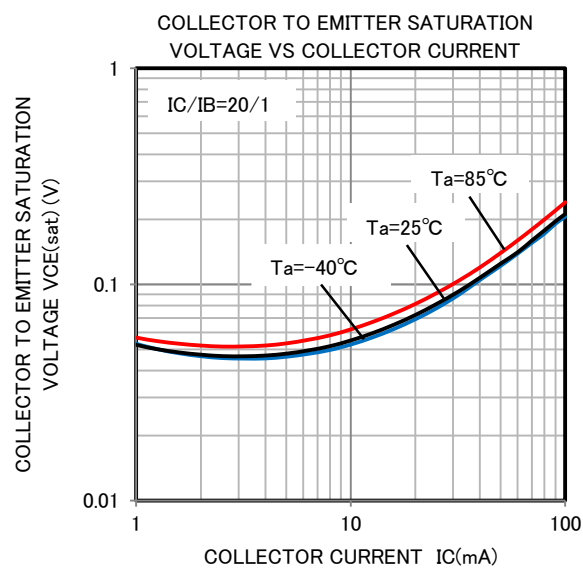
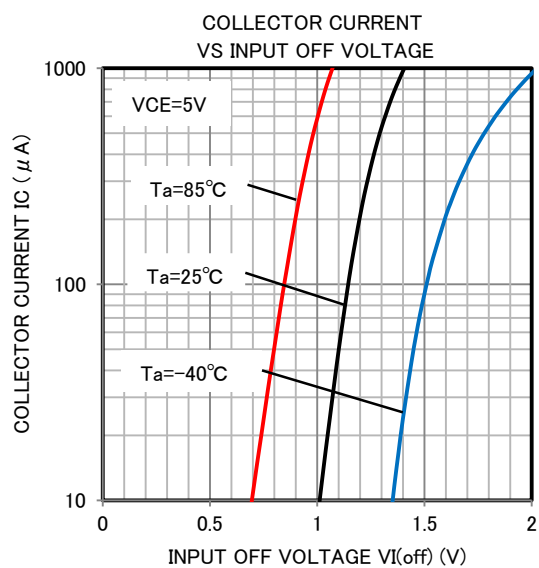
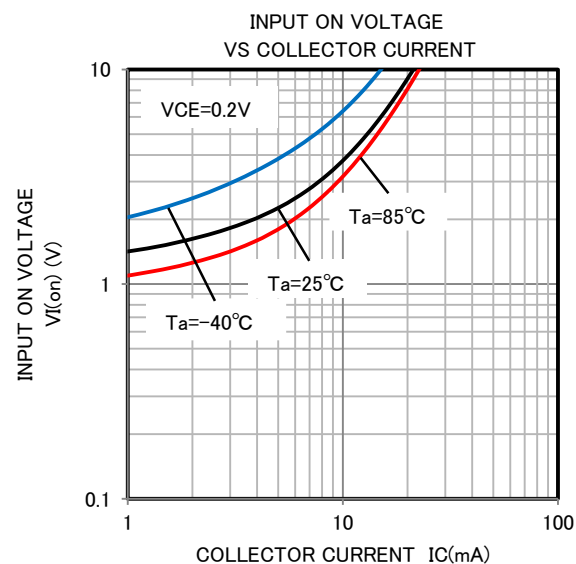
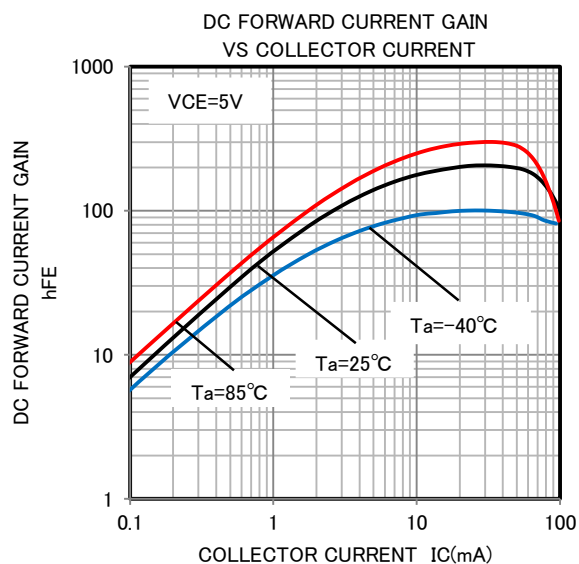
## MARKING



## ELECTRICAL CHARACTERISTICS (Ta=25°C)

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
I <sub>CB0</sub>	Collector cut off current	V <sub>CB</sub> =50V, I <sub>E</sub> =0A	—	—	0.1	μA
I <sub>EB0</sub>	Emitter cut off current	V <sub>EB</sub> =5V, I <sub>C</sub> =0A	41	53	76	μA
h <sub>FE</sub>	DC forward current gain	V <sub>CE</sub> =5V, I <sub>C</sub> =5mA	50	—	—	—
V <sub>CE(sat)</sub>	Collector to Emitter saturation voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA	—	—	0.3	V
V <sub>I(ON)</sub>	Input on voltage	V <sub>CE</sub> =0.2V, I <sub>C</sub> =5mA	—	2.2	5.0	V
V <sub>I(OFF)</sub>	Input off voltage	V <sub>CE</sub> =5V, I <sub>C</sub> =100μA	0.8	1.1	—	V
R <sub>1</sub>	Input resistor	—	33	47	61	kΩ
R <sub>2</sub> / R <sub>1</sub>	Resistor ratio	—	0.9	1.0	1.1	—
f <sub>T</sub>	Gain band width product	V <sub>CE</sub> =6V, I <sub>E</sub> =-10mA	—	200	—	MHz
V <sub>Z</sub>	Zener voltage	I <sub>Z</sub> =5mA	17.1	18	18.9	V
I <sub>R</sub>	Reverse current	V <sub>R</sub> =14V	—	—	1.0	μA

## TYPICAL CHARACTERISTICS (Tr)



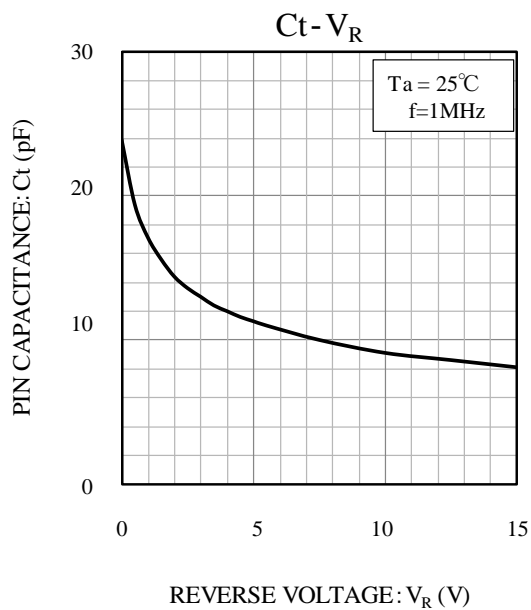
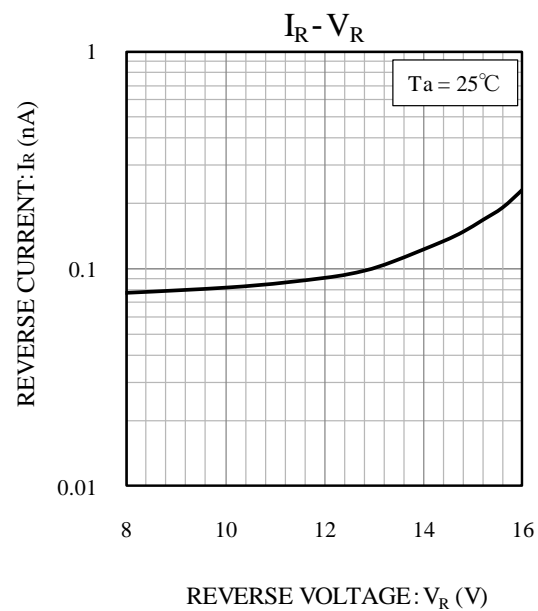
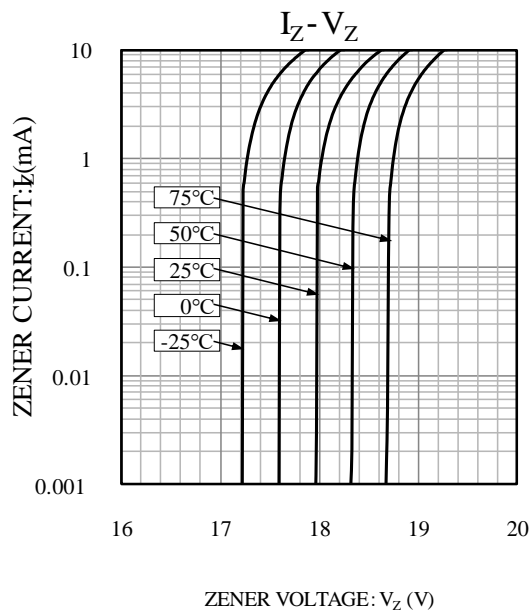
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## TYPICAL CHARACTERISTICS (Di)



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**Keep safety first in your circuit designs!**

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